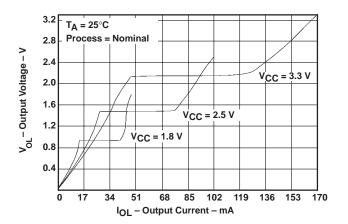
- **Member of the Texas Instruments** Widebus™ Family
- **EPIC™** (Enhanced-Performance Implanted **CMOS) Submicron Process**
- **DOC**[™] (Dynamic Output Control) Circuit **Dynamically Changes Output Impedance, Resulting in Noise Reduction Without Speed Degradation**
- **Dynamic Drive Capability Is Equivalent to** Standard Outputs With IOH and IOL of \pm 24 mA at 2.5-V V_{CC}
- Overvoltage-Tolerant Inputs/Outputs Allow **Mixed-Voltage-Mode Data Communications**

- I_{off} Supports Partial-Power-Down Mode Operation
- Ideal for Use in PC133 Registered DIMM **Applications**
- **ESD Protection Exceeds JESD 22**
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **Package Options Include Plastic Thin** Shrink Small-Outline (DGG) and Thin Very Small-Outline (DGV) Packages

description

A Dynamic Output Control (DOC) circuit is implemented, which, during the transition, initially lowers the output impedance to effectively drive the load and, subsequently, raises the impedance to reduce noise. Figure 1 shows typical V_{OI} vs I_{OI} and V_{OH} vs I_{OH} curves to illustrate the output impedance and drive capability of the circuit. At the beginning of the signal transition, the DOC circuit provides a maximum dynamic drive that is equivalent to a high-drive standard-output device. For more information, refer to the TI application reports, AVC Logic Family Technology and Applications, literature number SCEA006, and Dynamic Output Control (DOC™) Circuitry Technology and Applications, literature number SCEA009.



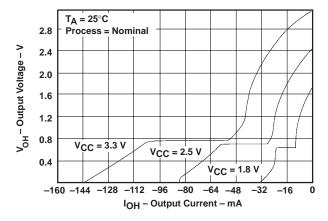


Figure 1. Output Voltage vs Output Current

This 16-bit universal bus driver is operational at 1.2-V to 3.6-V V_{CC}, but is designed specifically for 1.65-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable (OE) input. The device operates in the transparent mode when the latch-enable (\overline{LE}) input is low. When \overline{LE} is high, the A data is latched if the clock (CLK) input is held at a high or low logic level. If LE is high, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When OE is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DOC, EPIC, and Widebus are trademarks of Texas Instruments Incorporated.



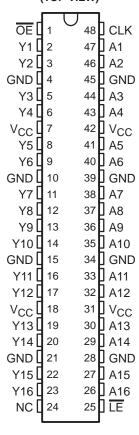
description (continued)

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74AVC16334 is characterized for operation from -40°C to 85°C.

terminal assignments

DGG OR DGV PACKAGE (TOP VIEW)



NC - No internal connection

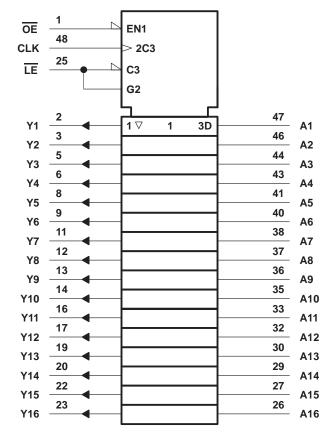
FUNCTION TABLE

	OUTPUT			
OE	LE	CLK	Α	Υ
Н	Х	Х	Χ	Z
L	L	X	L	L
L	L	X	Н	Н
L	Н	\uparrow	L	L
L	Н	\uparrow	Н	Н
L	Н	L or H	Χ	Y ₀ †

[†] Output level before the indicated steady-state input conditions were established

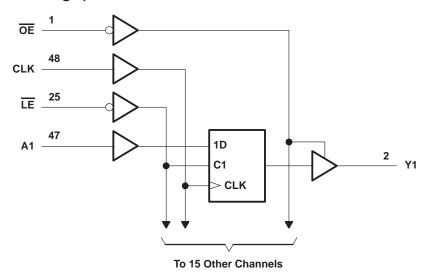


logic symbol†



[†]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





SCES154E - DECEMBER 1998 - REVISED SEPTEMBER 1999

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	. −0.5 V to 4.6 V
Input voltage range, V _I (see Note 1)	
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1)	. −0.5 V to 4.6 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	$/$ to V_{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	70°C/W
DGV package	58°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT		
Vac	Cumply yeltogo	Operating	1.65	3.6	V		
V _{CC} Su	Supply voltage	Data retention only	1.2		V		
		V _{CC} = 1.2 V	Vcc				
 {\/}	High-level input voltage	$V{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}		V		
VIH	r light-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		ľ		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2				
		V _{CC} = 1.2 V		GND			
 	Low level input veltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	V		
VIL	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8			
٧ _I	Input voltage		0	3.6	V		
V ₀	Output voltage	Active state	0	Vcc	V		
Vo	Output voltage	3-state	0	3.6	V		
		V _{CC} = 1.65 V to 1.95 V		-4			
lons	Static high-level output current [‡]	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-8	mA		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		-12			
		V _{CC} = 1.65 V to 1.95 V		4			
lols	Static low-level output current [‡]	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		8	mA		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		12			
Δt/Δν	Input transition rise or fall rate	V _{CC} = 1.65 V to 3.6 V		5	ns/V		
TA	Operating free-air temperature		-40	85	°C		

[‡] Dynamic drive capability is equivalent to standard outputs with I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}. See Figure 1 for V_{OL} vs I_{OL} and V_{OH} vs I_{OH} characteristics. Refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number **SCEA006**, and *Dynamic Output Control (DOC™) Circuitry Technology and Applications*, literature number **SCEA009**.

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST C	ONDITIONS	Vcc	MIN	TYP†	MAX	UNIT	
Voн		I _{OHS} = -100 μA	$I_{OHS} = -100 \mu A$		V _{CC} -0	.2			
		$I_{OHS} = -4 \text{ mA},$	V _{IH} = 1.07 V	1.65 V	1.2			V	
VOH		$I_{OHS} = -8 \text{ mA},$	V _{IH} = 1.7 V	2.3 V	1.75			V	
		$I_{OHS} = -12 \text{ mA},$	V _{IH} = 2 V	3 V	2.3				
		I _{OLS} = 100 μA		1.65 V to 3.6 V			0.2		
\/0.		$I_{OLS} = 4 \text{ mA},$	$V_{IL} = 0.57 V$	1.65 V			0.45	V	
VOL		$I_{OLS} = 8 \text{ mA},$	$V_{IL} = 0.7 V$	2.3 V			0.55	V	
	_	$I_{OLS} = 12 \text{ mA},$	$V_{IL} = 0.8 V$	3 V			0.7	Ļ	
lį	Control inputs	$V_I = V_{CC}$ or GND		3.6 V			±2.5	μΑ	
l _{off}		V_I or $V_O = 3.6 V$		0			±10	μΑ	
loz		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ	
ICC		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ	
	CLK input	V _I = V _{CC} or GND	V. Vaaar CND			4			
	CER input	AL = ACC OLGIND		3.3 V		4			
Ci	Control inputs	$V_I = V_{CC}$ or GND		2.5 V		4		pF	
^U	Control inputs	AL = ACC OLOUP		3.3 V		4		ρı	
	Data inputs	Vi = Vo a or GND	V _I = V _{CC} or GND			2.5			
	Data Inputs	AL = ACC OLGUAD				2.5			
Со	Outputs	V- V or CND		2.5 V		6.5		pF	
	Outputs	$V_O = V_{CC}$ or GND		3.3 V		6.5		PΓ	

[†] Typical values are measured at $T_A = 25$ °C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

				V _{CC} = 1.2 V		V _{CC} = 1.5 V ± 0.1 V		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock freq	uency							150		150		150	MHz
	Pulse	LE low						3.3		3.3		3.3		no
t _W	duration	CLK high or low						3.3		3.3		3.3		ns
		Data before CLK↑		1		0.8		0.7		0.7		0.7		
t _{su}	Setup	Data	CLK high	0.8		0.9		0.9		0.9		0.9		ns
	timo		CLK low	2.7		1.6		1.2		1		1		
^t h	Hold time	Data after CLK↑		1.3		1.1		0.9		0.8		0.7		ns
4.	Hold		CLK high	2.2		1.9		1.7		1.5	·	1.5		ns
th	time		CLK low	2.4		1.8		1.6		1.4		1.3		ns

SCES154E - DECEMBER 1998 - REVISED SEPTEMBER 1999

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

PARAMETER	FROM TO (INPUT)		V _{CC} = 1.2 V	V _{CC} = 1.5 V ± 0.1 V		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INFO1)	(0011-01)	TYP	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}						150		150		150		MHz
	А		5.3	1.2	6.2	1.6	4.9	1.2	3.1	0.9	2.5	
t _{pd}	LE	Υ	7	2.2	9.7	2.1	7.5	1.5	4.9	1.2	4	ns
	CLK		6	1.9	7.8	1.8	6	1.3	3.7	1	3.1	
t _{en}	OE	Υ	7.9	2.4	10.2	2.2	8.8	1.5	6.7	1.2	6.2	ns
^t dis	ŌĒ	Υ	7.7	2.7	10.3	2.6	8.4	1.2	5.3	1.1	5.3	ns

switching characteristics, $T_A = 0$ °C to 85°C, $C_L = 0$ pF †

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1	UNIT	
	(1141 01)	(6611.61)	MIN	MAX	
t _{and}	А	~	0.6	1.3	
^t pd	CLK	Ť	0.7	1.5	ns

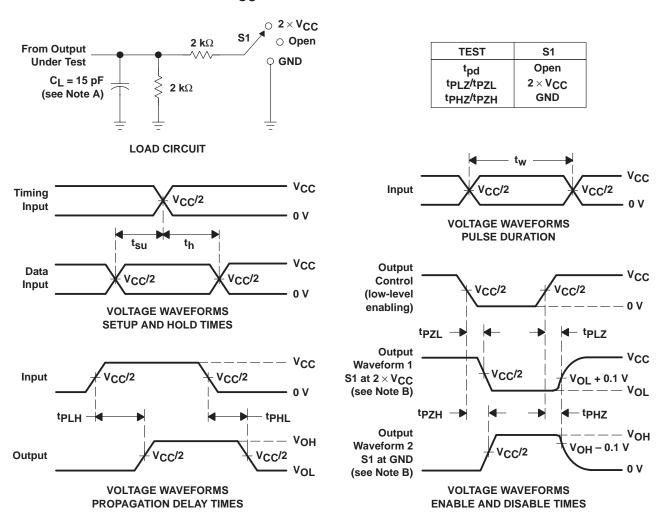
[†] Texas Instruments SPICE simulation data

operating characteristics, T_A = 25°C

PARAMETER			TEST CO	MULTIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT
			TEST CONDITIONS		TYP	TYP	TYP	UNIT
	Power dissipation	Outputs enabled	C. 0	f 40 MH I=	45	48	52	pF
C _{pd}	capacitance	Outputs disabled	$C_L = 0$,	f = 10 MHz	23	25	28	рг



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.2 \text{ V}$ AND 1.5 V \pm 0.1 V

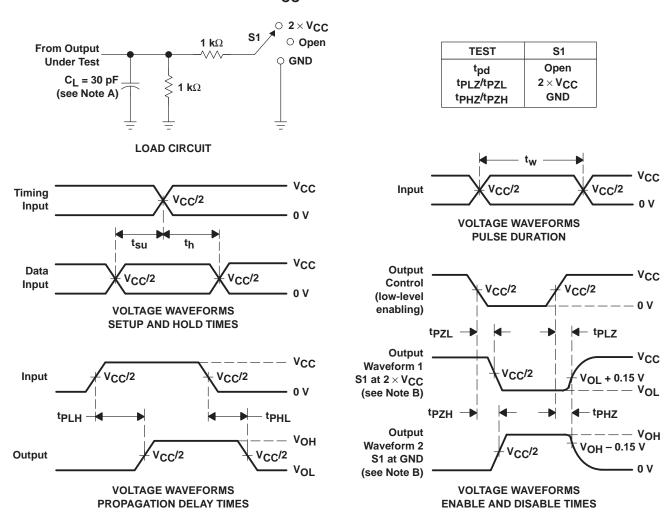


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

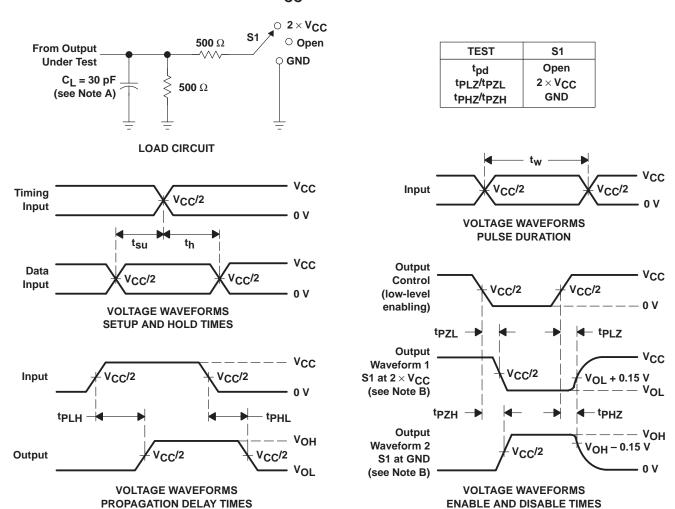


- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns, $t_f \leq 2$ ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

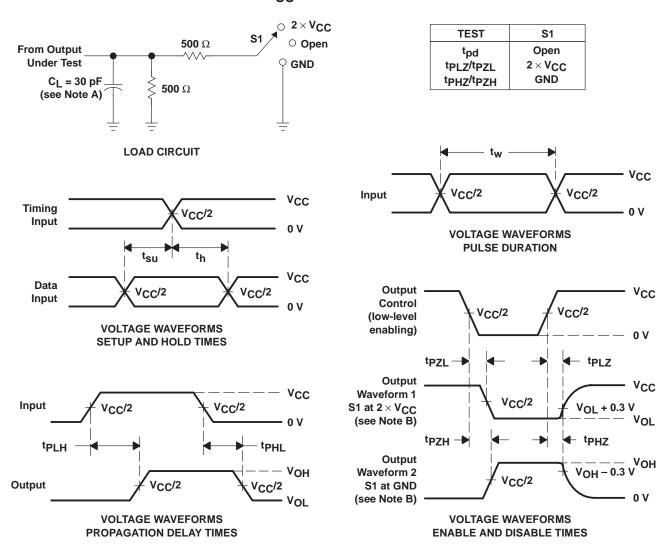


- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \ \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$



NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \ \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 5. Load Circuit and Voltage Waveforms



IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1999, Texas Instruments Incorporated